

## Dual 3-Input "NOR" Gate Plus Inverter

The MC14000UB dual 3-input NOR gate plus inverter is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired.

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Logic Swing Independent of Fanout
- Pin-for-Pin Replacement for CD4000UB

### MAXIMUM RATINGS\* (Voltages Referenced to $V_{SS}$ )

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage	- 0.5 to + 18.0	V
$V_{in}, V_{out}$	Input or Output Voltage (DC or Transient)	- 0.5 to $V_{DD} + 0.5$	V
$I_{in}, I_{out}$	Input or Output Current (DC or Transient), per Pin	$\pm 10$	mA
$P_D$	Power Dissipation, per Package†	500	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature (8-Second Soldering)	260	°C

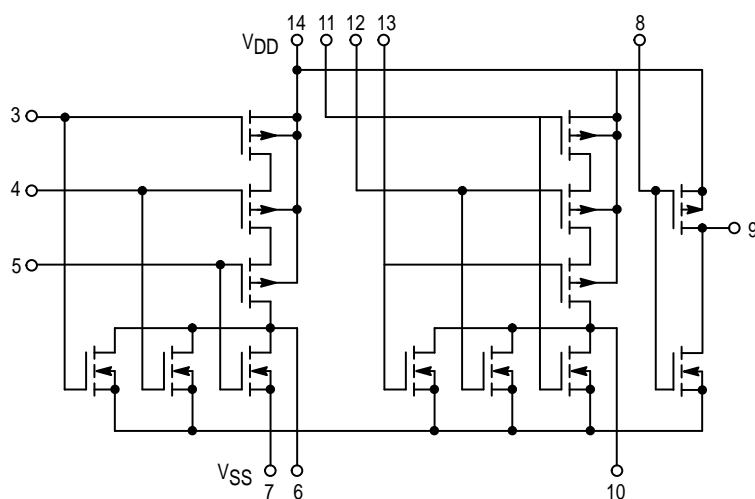
\* Maximum Ratings are those values beyond which damage to the device may occur.

† Temperature Derating:

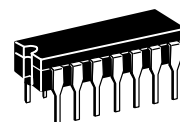
Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C

Ceramic "L" Packages: - 12 mW/°C From 100°C To 125°C

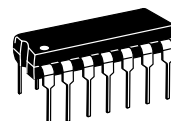
### CIRCUIT SCHEMATIC



## MC14000UB



**L SUFFIX**  
CERAMIC  
CASE 632



**P SUFFIX**  
PLASTIC  
CASE 646



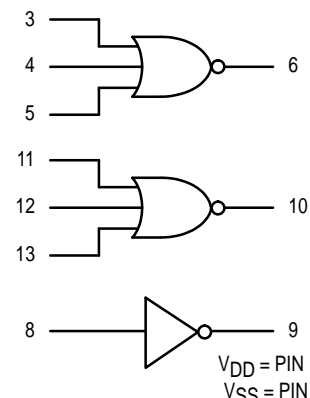
**D SUFFIX**  
SOIC  
CASE 751A

### ORDERING INFORMATION

MC14XXXUBCP Plastic  
MC14XXXUBCL Ceramic  
MC14XXXUBD SOIC

$T_A = -55^\circ$  to  $125^\circ\text{C}$  for all packages.

### LOGIC DIAGRAM



### PIN ASSIGNMENT

NC	1	14	$V_{DD}$
NC	2	13	IN 3B
IN 1A	3	12	IN 2B
IN 2A	4	11	IN 1B
IN 3A	5	10	OUTB
OUTA	6	9	OUTC
$V_{SS}$	7	8	IN 1C

NC = NO CONNECTION

**ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

Characteristic	Symbol	V <sub>DD</sub> Vdc	– 55°C		25°C			+ 125°C		Unit
			Min	Max	Min	Typ #	Max	Min	Max	
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	V <sub>OL</sub>	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
	V <sub>OH</sub>	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage (V <sub>O</sub> = 4.5 Vdc) (V <sub>O</sub> = 9.0 Vdc) (V <sub>O</sub> = 13.5 Vdc)	V <sub>IL</sub>	5.0	—	1.0	—	2.25	1.0	—	1.0	Vdc
		10	—	2.0	—	4.50	2.0	—	2.0	
		15	—	2.5	—	6.75	2.5	—	2.5	
	V <sub>IH</sub>	5.0	4.0	—	4.0	2.75	—	4.0	—	Vdc
		10	8.0	—	8.0	5.50	—	8.0	—	
		15	12.5	—	12.5	8.25	—	12.5	—	
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	Source I <sub>OH</sub>	5.0	– 1.2	—	– 1.0	– 1.7	—	– 0.7	—	mA <sub>dc</sub>
		5.0	– 0.25	—	– 0.2	– 0.36	—	– 0.14	—	
		10	– 0.62	—	– 0.5	– 0.9	—	– 0.35	—	
		15	– 1.8	—	– 1.5	– 3.5	—	– 1.1	—	
	Sink I <sub>OL</sub>	5.0	0.64	—	0.51	0.88	—	0.36	—	mA <sub>dc</sub>
		10	1.6	—	1.3	2.25	—	0.9	—	
		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I <sub>in</sub>	15	—	± 0.1	—	± 0.00001	± 0.1	—	± 1.0	μA <sub>dc</sub>
Input Capacitance (V <sub>in</sub> = 0)	C <sub>in</sub>	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0	—	0.25	—	0.0005	0.25	—	7.5	μA <sub>dc</sub>
		10	—	0.5	—	0.0010	0.5	—	15	
		15	—	1.0	—	0.0015	1.0	—	30	
Total Supply Current**† (Dynamic plus Quiescent, Per Gate, C <sub>L</sub> = 50 pF)	I <sub>T</sub>	5.0 10 15	I <sub>T</sub> = (0.3 μA/kHz) f + I <sub>DD</sub> /N I <sub>T</sub> = (0.6 μA/kHz) f + I <sub>DD</sub> /N I <sub>T</sub> = (0.8 μA/kHz) f + I <sub>DD</sub> /N							μA <sub>dc</sub>

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

\*\*The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) V f k$$

where: I<sub>T</sub> is in μH (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> – V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range V<sub>SS</sub> ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>DD</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V<sub>SS</sub> or V<sub>DD</sub>). Unused outputs must be left open.

# SWITCHING CHARACTERISTICS\* ( $C_L = 50 \text{ pF}$ , $T_A = 25^\circ\text{C}$ )

Characteristic	Symbol	$V_{DD}$ Vdc	Min	Typ #	Max	Unit
Output Rise Time $t_{TLH} = (3.0 \text{ ns/pF}) C_L + 30 \text{ ns}$ $t_{TLH} = (1.5 \text{ ns/pF}) C_L + 15 \text{ ns}$ $t_{TLH} = (1.1 \text{ ns/pF}) C_L + 10 \text{ ns}$	$t_{TLH}$	5.0 10 15	— — —	180 90 65	360 180 130	ns
Output Fall Time $t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ $t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ $t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	$t_{THL}$	5.0 10 15	— — —	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) C_L + 30 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) C_L + 22 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.50 \text{ ns/pF}) C_L + 15 \text{ ns}$	$t_{PLH}, t_{PHL}$	5.0 10 15	— — —	115 55 40	230 110 80	ns

\* The formulas given are for the typical characteristics only at  $25^\circ\text{C}$ .

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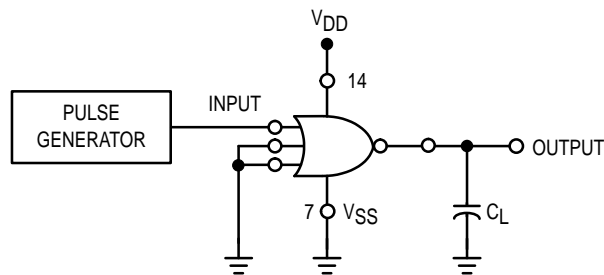


Figure 1. Switching Time Test Circuit and Waveforms

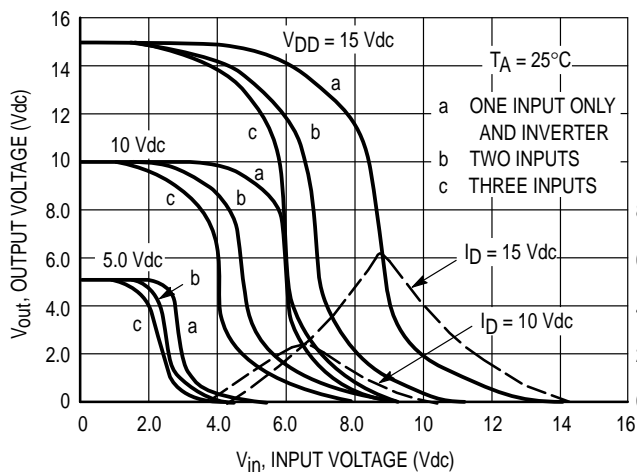


Figure 2. Typical Voltage and Current Transfer Characteristics

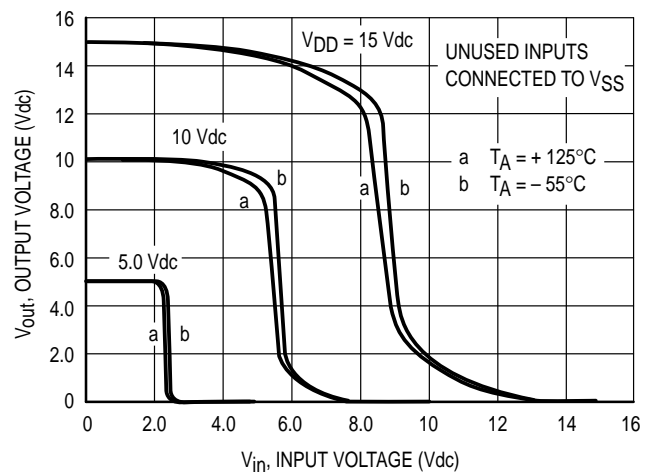
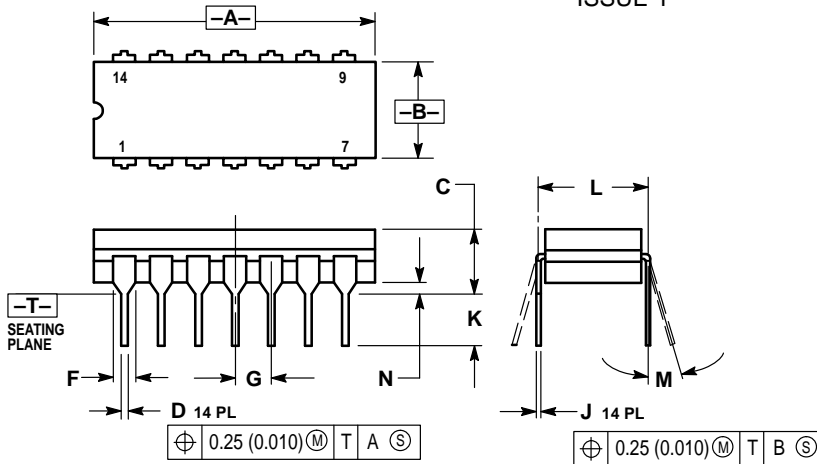


Figure 3. Typical Voltage Transfer Characteristics versus Temperature

## OUTLINE DIMENSIONS

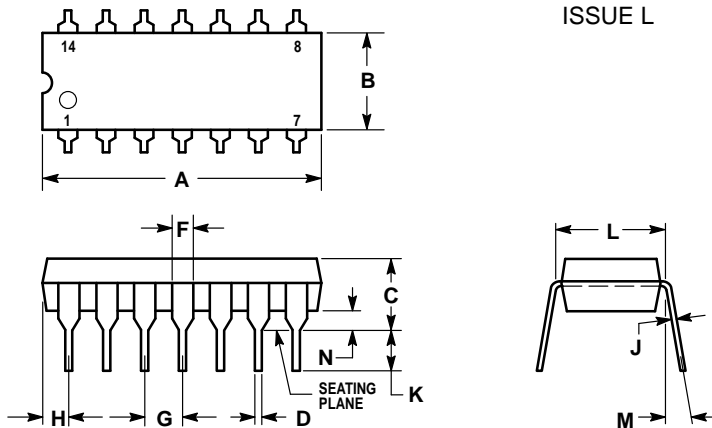
### L SUFFIX CERAMIC DIP PACKAGE CASE 632-08 ISSUE Y



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.94
B	0.245	0.280	6.23	7.11
C	0.155	0.200	3.94	5.08
D	0.015	0.020	0.39	0.50
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

### P SUFFIX PLASTIC DIP PACKAGE CASE 646-06 ISSUE L

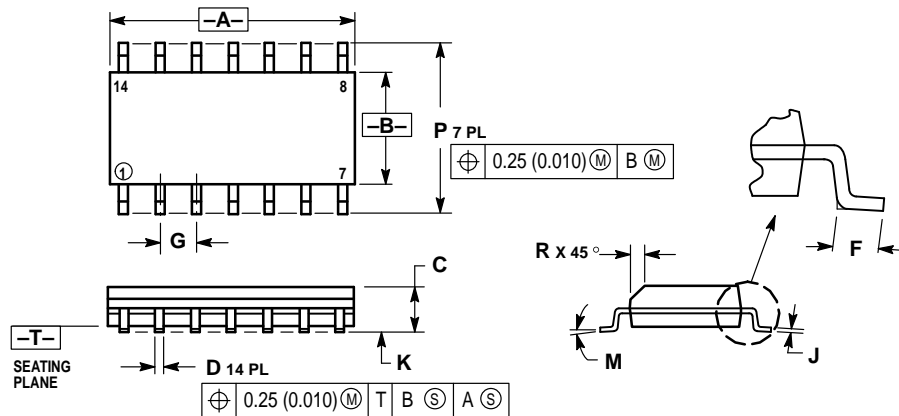


- NOTES:
1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
  2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  4. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

## OUTLINE DIMENSIONS


### D SUFFIX PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

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#### How to reach us:

**USA/EUROPE/Locations Not Listed:** Motorola Literature Distribution;  
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447 or 602-303-5454

**MFAX:** RMFAX0@email.sps.mot.com – TOUCHTONE 602-244-6609  
**INTERNET:** http://Design-NET.com

**JAPAN:** Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, 6F Seibu-Butsuryu-Center,  
3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-81-3521-8315

**ASIA/PACIFIC:** Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,  
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



MC14000UB/D

